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**Substitute for form 1449/PTO**

## **INFORMATION DISCLOSURE STATEMENT BY APPLICANT**

*(Use as many sheets as necessary)*

Sheet 1 of 2

***Complete if Known***

Application Number	Nat'l Stage of PCT/JP2005/012886
Filing Date	July 13, 2005 [371(c) date]
First Named Inventor	Seiji Nakahata
Art Unit	(To be assigned) 2826
Examiner Name	(To be assigned) Evan Pert
Attorney Docket Number	39.070

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages Or Relevant Figures Appear	T <sup>6</sup>
		Country Code <sup>3</sup> - Number <sup>4</sup> - Kind Code <sup>5</sup> (if known)				
F1	JP-2004-189549-A		07-08-2004	Sumitomo Metal Mining		✓
F2	WO-02/099169-A1		12-12-2002	New Industry Research		✓
F3	JP-2004-277224-A		10-07-2004	Ricoh		✓
F4	JP-2001-058900-A		03-06-2001	Ricoh		✓
F5	JP-2002-047100-A		02-12-2002	Nippon Pillar Packing		✓

Examiner Signature	/Evan Pert/	Date Considered	08/17/2008
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Sheet	2	of	2	Attorney Docket Number	39.070

## NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
	O1	M. AOKI, et al., "Conditions for Seeded Growth of GaN Crystals by the Na Flux Method," Materials Letters, 2002, vol. 56, pp. 660-664	
	O2	H. YAMANE, et al., "GaN Single Crystal Growth by the Flux Method," Applied Physics 2002, vol. 71, no. 5, pp. 548-552	✓
	O3	S. DHAR, et al., "Observation of a 0.7 eV Electron Trap in Dilute GaAsN Layers Grown by Liquid Phase Epitaxy," Applied Physics Letters, 9 August 2004, vol. 85, no. 6, pp. 964-966	
	O4	H. MORKOC, "Comprehensive Characterization of Hydride VPE Grown GaN Layers and Templates," Materials Science and Engineering, R33, 2001, pp. 135-207	

Examiner Signature	/Evan Pert/	Date Considered	08/17/2008
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